PSMN3R4-30BLE

N-channel 30 V 3.4 mΩ logic level MOSFET in D2PAK

12 October 2012 Product data sheet

1. Product profile

1.1 General description

Logic level N-channel MOSFET in D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Enhanced forward biased safe operating area for superior linear mode operation
- Very low Rdson for low conduction losses

1.3 Applications

- Electronic fuse
- Hot swap
- Load switch
- Soft start

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	-	30	V
I_D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; Fig. 1	[1]	-	-	120	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 2		-	-	178	W
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 12		-	2.95	3.4	mΩ
		V_{GS} = 4.5 V; I_D = 25 A; T_j = 25 °C; Fig. 12		-	4.25	5	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	V_{GS} = 4.5 V; I_D = 25 A; V_{DS} = 15 V; Fig. 14; Fig. 15		-	12.2	-	nC
$Q_{G(tot)}$	total gate charge	V_{GS} = 10 V; I_D = 25 A; V_{DS} = 15 V; Fig. 14; Fig. 15		-	81	-	nC

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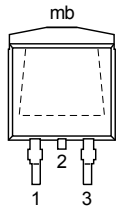
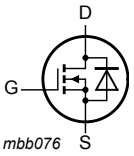
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Avalanche ruggedness							
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; V_{sup} ≤ 30 V; unclamped; R_{GS} = 50 Ω; Fig. 3		-	-	246	mJ

[1] Capped at 120A due to package

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 D2PAK (SOT404)	
2	D	drain[1]		
3	S	source		
mb	D	mounting base; connected to drain		

[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN3R4-30BLE	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Marking

Table 4. Marking codes

Type number	Marking code
PSMN3R4-30BLE	PSMN3R4-30BLE

5. Limiting values

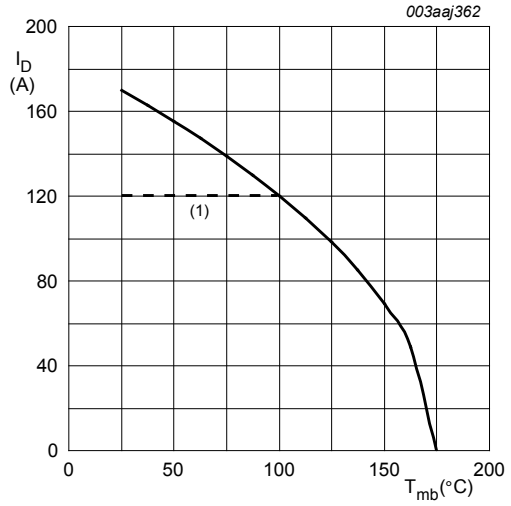
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T_j ≥ 25 °C; T_j ≤ 175 °C		-	30	V
V_{DGR}	drain-gate voltage	T_j ≤ 175 °C; T_j ≥ 25 °C; R_{GS} = 20 kΩ		-	30	V

Symbol	Parameter	Conditions		Min	Max	Unit
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	V_{GS} = 10 V; T_{mb} = 100 °C; Fig. 1		-	119	A
		V_{GS} = 10 V; T_{mb} = 25 °C; Fig. 1	[1]	-	120	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10$ µs; T_{mb} = 25 °C; Fig. 4		-	672	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 2		-	178	W
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain diode						
I_S	source current	T_{mb} = 25 °C	[1]	-	120	A
I_{SM}	peak source current	pulsed; $t_p \leq 10$ µs; T_{mb} = 25 °C		-	672	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; $V_{sup} \leq 30$ V; unclamped; R_{GS} = 50 Ω; Fig. 3		-	246	mJ

[1] Capped at 120A due to package



(1) Capped at 120A due to package

Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \geq 10V$$

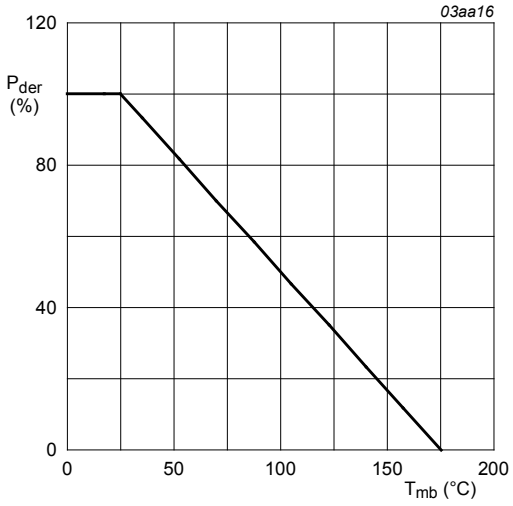


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

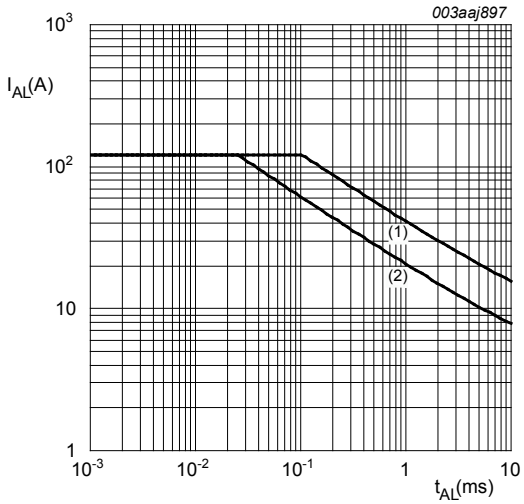


Fig. 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j\ (init)} = 25°C$; (2) $T_{j\ (init)} = 100°C$

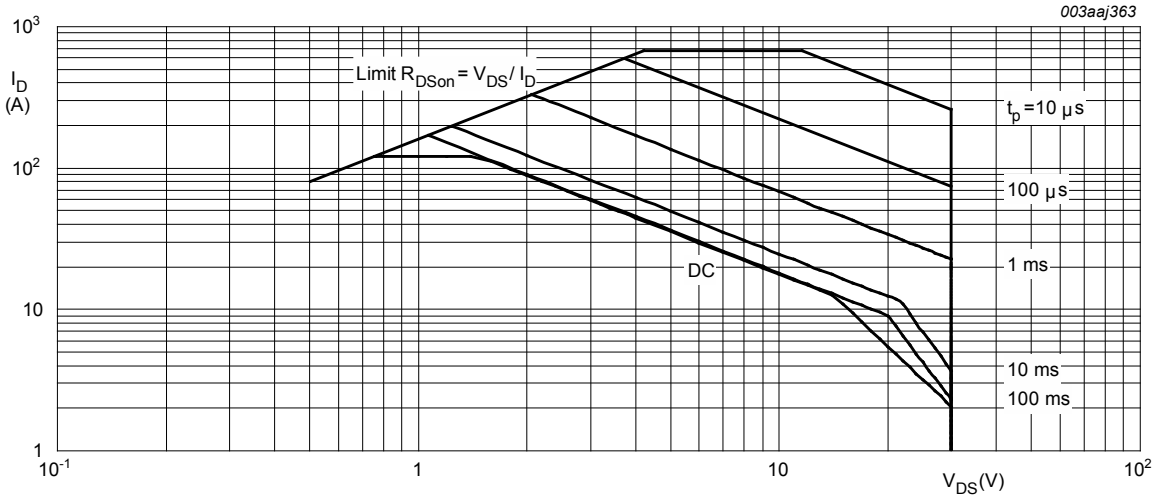


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25°C$; I_{DM} *is a single pulse*

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j\text{-}mb)}$	thermal resistance from junction to mounting base	Fig. 5		-	0.73	0.84	K/W
$R_{th(j\text{-}a)}$	thermal resistance from junction to ambient	minimum footprint; FR4 board		-	50	-	K/W

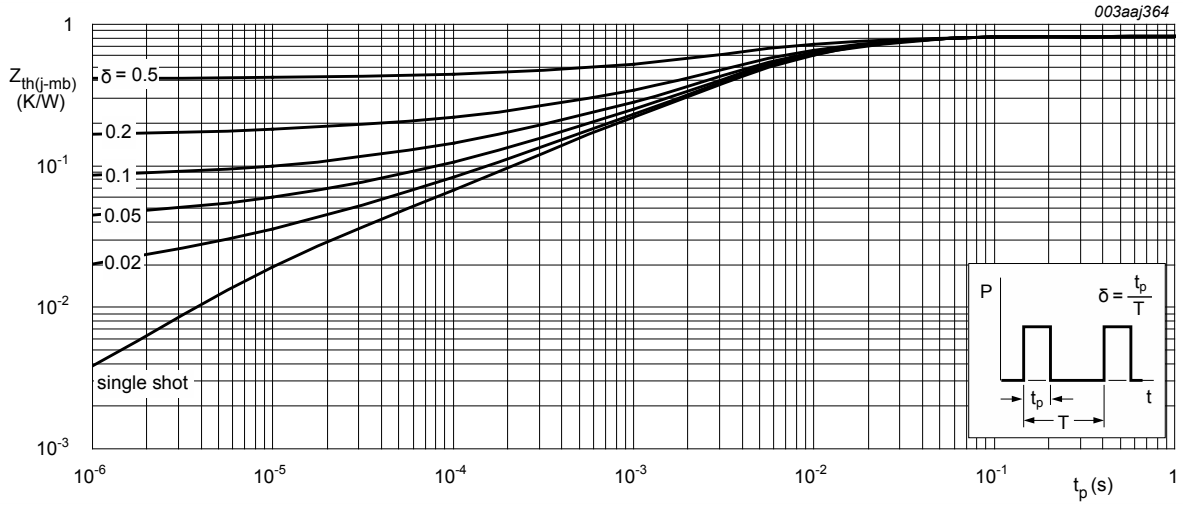


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C		27	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		30	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; Fig. 10		0.5	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; Fig. 11; Fig. 10		1.3	1.7	2.15	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; Fig. 10		-	-	2.45	V
I_{DSS}	drain leakage current	V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 °C		-	0.2	5	µA
		V_{DS} = 30 V; V_{GS} = 0 V; T_j = 100 °C		-	-	100	µA
I_{GSS}	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C		-	10	100	nA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C		-	10	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 12		-	2.95	3.4	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; Fig. 13; Fig. 12		-	-	5.1	mΩ
		V_{GS} = 4.5 V; I_D = 25 A; T_j = 25 °C; Fig. 12		-	4.25	5	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; Fig. 13; Fig. 12		-	-	6.5	mΩ

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R_G	internal gate resistance (AC)	f = 1 MHz		0.5	1	2	Ω
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	I_D = 25 A; V_{DS} = 15 V; V_{GS} = 10 V; Fig. 14; Fig. 15		-	81	-	nC
		I_D = 25 A; V_{DS} = 15 V; V_{GS} = 4.5 V; Fig. 14; Fig. 15		-	37	-	nC
		I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V		-	79	-	nC
Q_{GS}	gate-source charge	I_D = 25 A; V_{DS} = 15 V; V_{GS} = 4.5 V; Fig. 14; Fig. 15		-	13.9	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge			-	7.5	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge			-	6.4	-	nC
Q_{GD}	gate-drain charge			-	12.2	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I_D = 25 A; V_{DS} = 15 V; Fig. 14; Fig. 15		-	3.2	-	V
C_{iss}	input capacitance	V_{DS} = 15 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; Fig. 16		-	4682	-	pF
C_{oss}	output capacitance			-	909	-	pF
C_{rss}	reverse transfer capacitance			-	438	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 15 V; R_L = 0.6 Ω; V_{GS} = 4.5 V; $R_{G(ext)}$ = 4.7 Ω; T_j = 25 °C		-	35.7	-	ns
t_r	rise time			-	101	-	ns
$t_{d(off)}$	turn-off delay time			-	49	-	ns
t_f	fall time			-	51.2	-	ns
Source-drain diode							
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; Fig. 17		-	0.85	1.2	V
t_{rr}	reverse recovery time	I_S = 25 A; dI_S/dt = 100 A/µs; V_{GS} = 0 V; V_{DS} = 15 V		-	37	-	ns
Q_r	recovered charge			-	38	-	nC

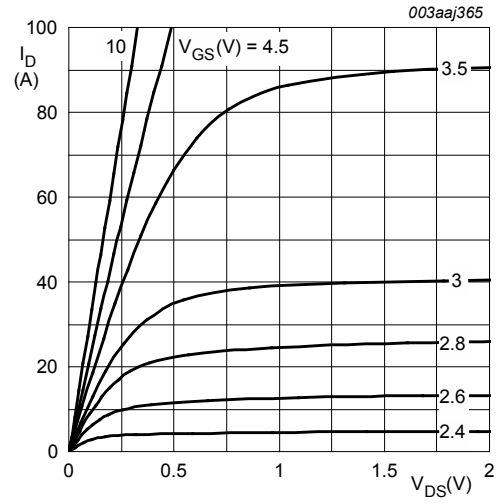


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

$T_j = 25°C$

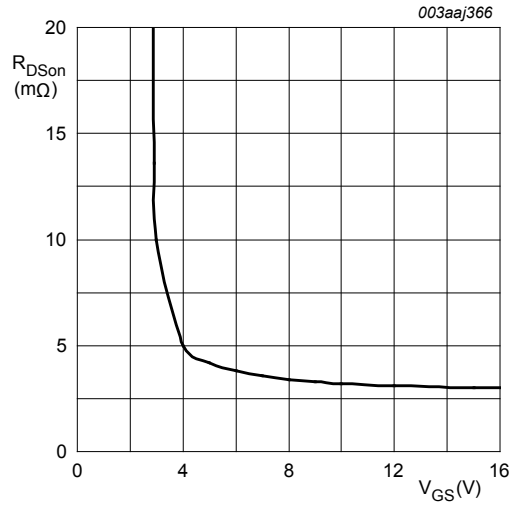


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25°C;\ I_D = 25A$

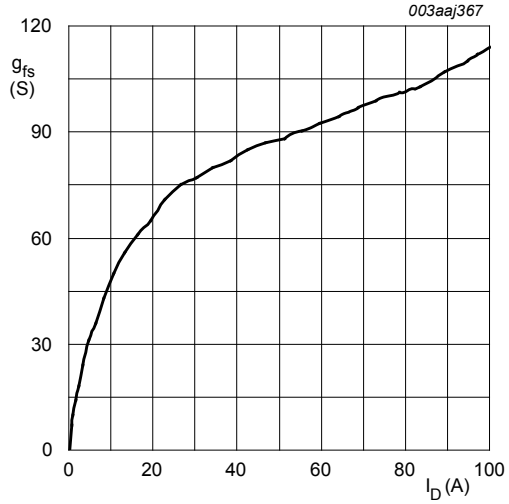


Fig. 8. Forward transconductance as a function of drain current; typical values

$T_j = 25°C;\ V_{DS} = 10V$

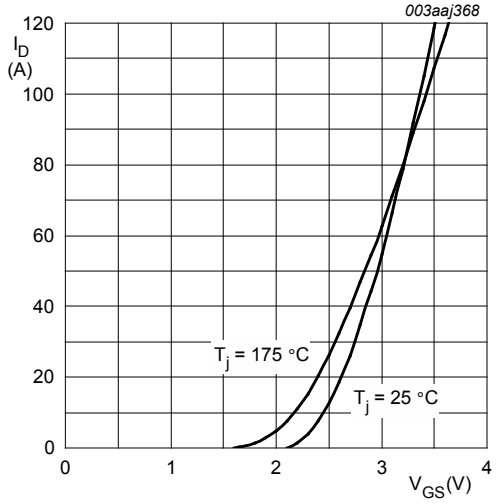


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10V$

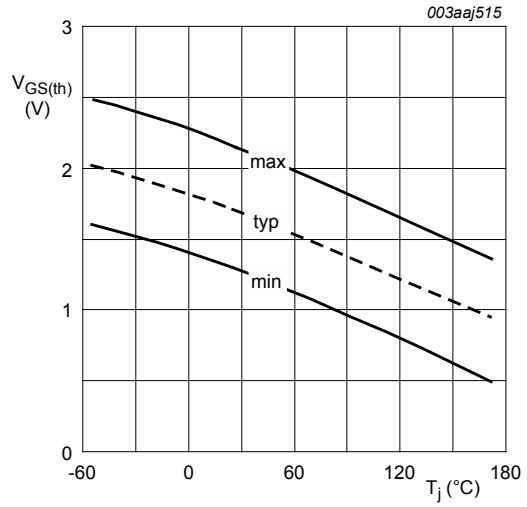


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$V_{DS} = V_{GS}$

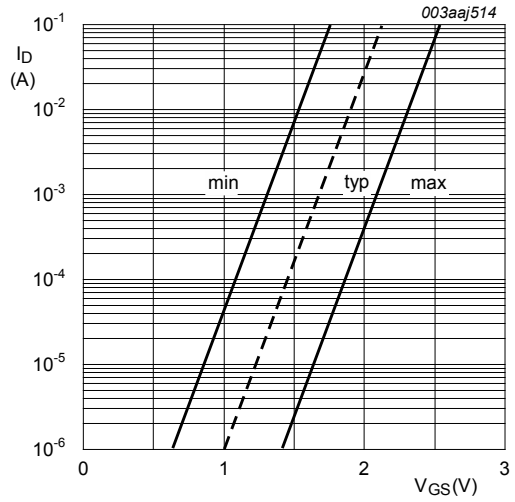


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25°C;\ V_{DS} = 5V$

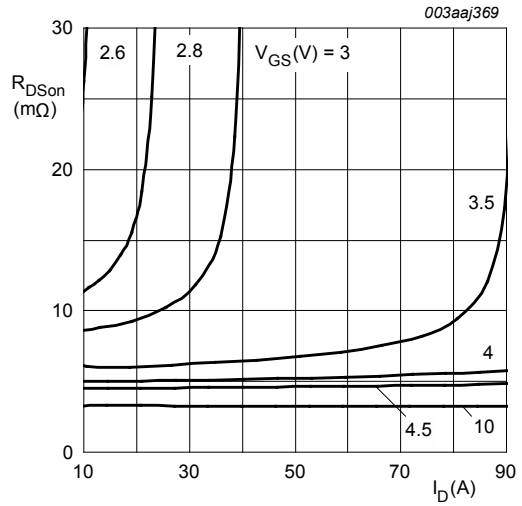


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$T_j = 25°C$

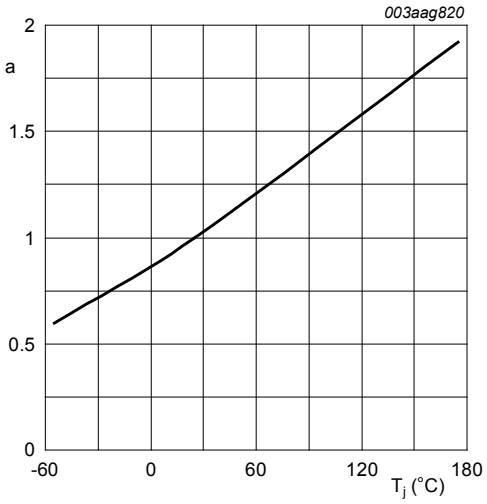


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25\,°C)}}$$

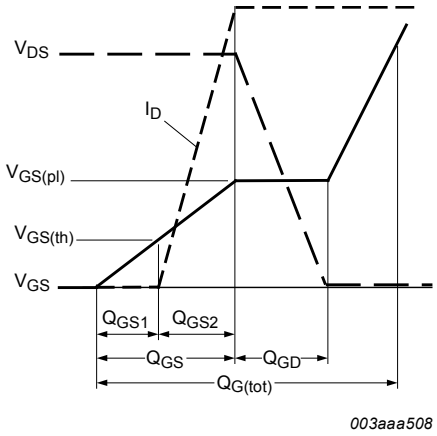


Fig. 14. Gate charge waveform definitions

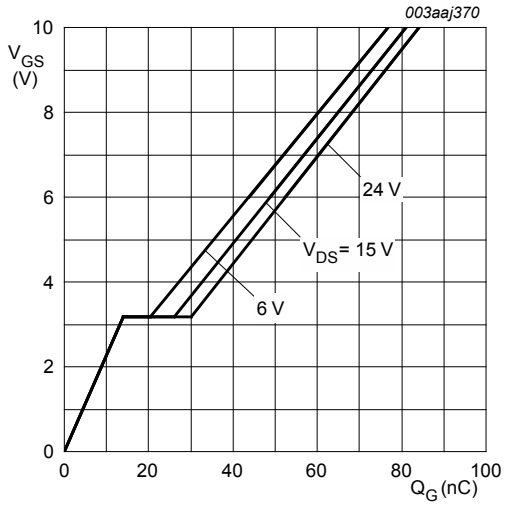


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$T_j = 25°C;\ I_D = 25A$

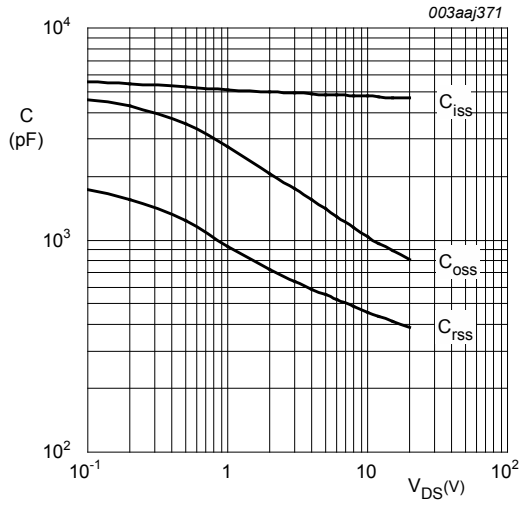


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0V;\ f = 1MHz$

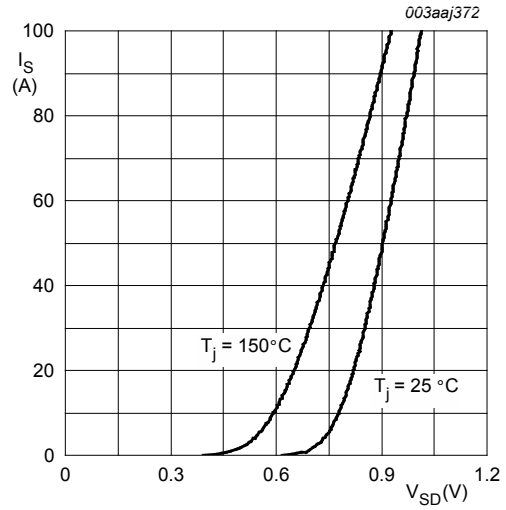
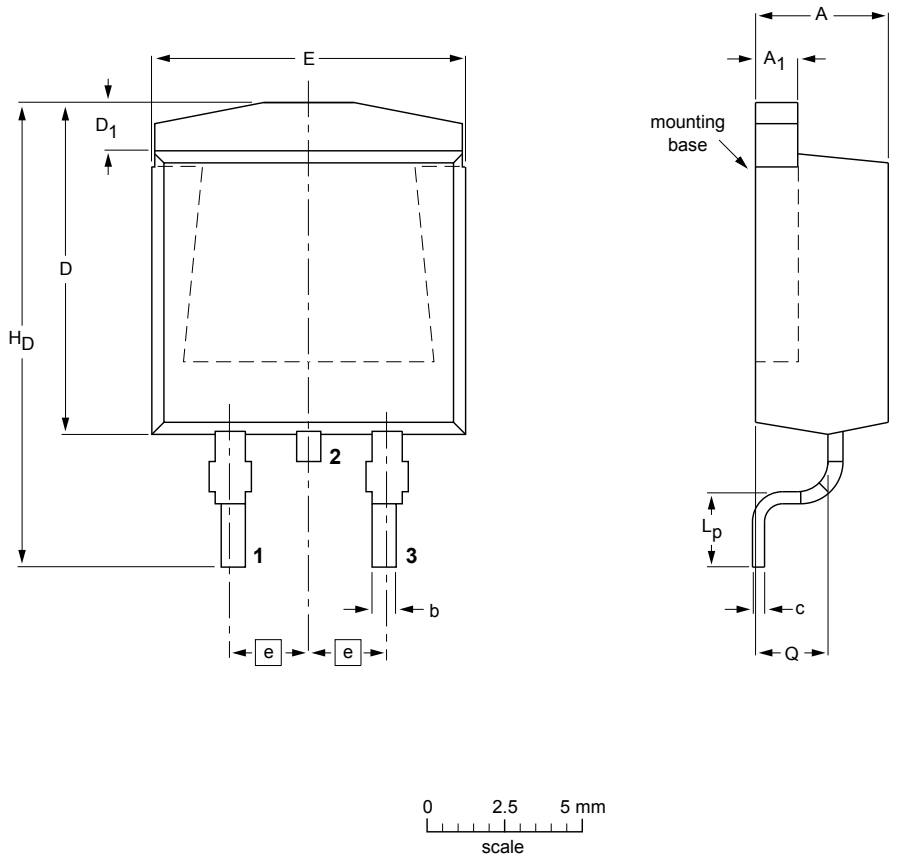


Fig. 17. Source current as a function of source-drain voltage; typical values

$V_{GS} = 0V$

8. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) **SOT404**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	c	D max.	D_1	E	e	L_p	H_D	Q
mm	4.50 4.10	1.40 1.27	0.85 0.60	0.64 0.46	11	1.60 1.20	10.30 9.70	2.54	2.90 2.10	15.80 14.80	2.60 2.20

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT404						~~05-02-11~~ 06-03-16

Fig. 18. Package outline D2PAK (SOT404)

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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